September 2009



H11AG1M Phototransistor Optocoupler

Features

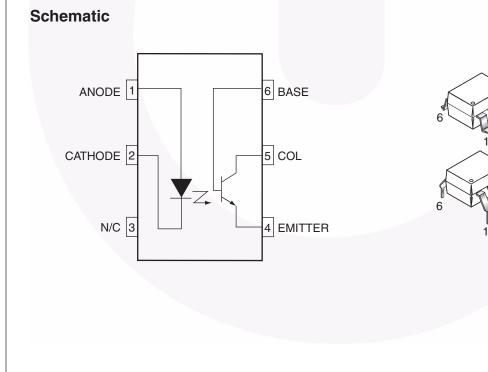
- High efficiency low degradation liquid epitaxial IRED
- Logic level compatible, input and output currents, with CMOS and LS/TTL
- High DC current transfer ratio at low input currents (as low as 200µA)
- Underwriters Laboratory (UL) recognized File #E90700, Volume 2
- IEC 60747-5-2 approved (ordering option V)

Applications

- CMOS driven solid state reliability
- Telephone ring detector
- Digital logic isolation

Description

The H11AG1M device consists of a Gallium-Aluminum-Arsenide IRED emitting diode coupled with a silicon phototransistor in a dual in-line package. This device provides the unique feature of the high current transfer ratio at both low output voltage and low input current. This makes it ideal for use in low power logic circuits, telecommunications equipment and portable electronics isolation applications.



查询"H11AG1M"供应商

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Parameters	Value	Units		
TOTAL DEVICE					
T _{STG}	Storage Temperature	-55 to +150	°C		
T _{OPR}	Operating Temperature	-40 to +100	°C		
T _{SOL}	Lead Solder Temperature (Wave Solder)	260 for 10 sec	°C		
PD	Total Device Power Dissipation @ 25°C (LED plus detector)	260	mW		
	Derate Linearly From 25°C	3.5	mW/°C		
EMITTER					
۱ _F	Continuous Forward Current	50	mA		
V _R	Reverse Voltage	6	V		
l _F (pk)	Forward Current – Peak (1µs pulse, 300pps)	3.0	А		
PD	LED Power Dissipation 25°C Ambient	75	mW		
	Derate Linearly From 25°C	1.0	mW/°C		
DETECTOR					
PD	Detector Power Dissipation @ 25°C	150	mW		
	Derate Linearly from 25°C	2.0	mW/°C		
Ι _C	Continuous Collector Current	50	mA		

查询"H11AG1M"供应商 Electrical Characteristics (T_A = 25°C unless otherwise specified.)

Individual Component Characteristics

Symbol	Parameters	Test Conditions	Min.	Тур.*	Max.	Units
EMITTER			-		1	
V _F	Input Forward Voltage	I _F = 1mA		1.25	1.5	V
I _R	Reverse Leakage Current	V _R = 5V, T _A = 25°C			10	μA
CJ	Capacitance	V = 0, f = 1.0MHz			100	pF
DETECTO	R		-		1	
BV _{CEO}	Breakdown Voltage, Collector to Emitter	I _C = 1.0mA, I _F = 0	30			V
BV_{CBO}	Collector to Base	I _C = 100μA, I _F = 0	70			V
BV _{ECO}	Emitter to Collector	I _C = 100μA, I _F = 0	7			V
I _{CEO}	Leakage Current, Collector to Emitter	V _{CE} = 10V, I _F = 0		5	10	μA
C _{CE}	Capacitance	V _{CE} = 10V, f = 1MHz		10		pF

*Typical values at $T_A = 25^{\circ}C$.

Isolation Characteristics

Symbol	Parameter	Test Conditions	Min.	Тур.*	Max.	Units
V _{ISO}	Input-Output Isolation Voltage	f = 60Hz, t = 1 sec.	7500			V _{AC} PEAK
R _{ISO}	Isolation Resistance	V _{I-O} = 500VDC, T _A = 25°C	10 ¹¹			Ω

Transfer Characteristics ($T_A = 25^{\circ}C$ Unless otherwise specified.)

		• • •				
Symbol	Characteristics	Test Conditions	Min.	Тур.*	Max.	Units
DC CHARAC	CTERISTICS					
CTR	Current Transfer Ratio	I _F = 1mA, V _{CE} = 5V	300			%
		I _F = 1mA, V _{CE} = 0.6V	100			
		I _F = 0.2mA, V _{CE} = 1.5V	100			
V _{CE(SAT)}	Saturation Voltage	I _F = 2.0mA, I _C = 0.5mA			.40	V
AC CHARAC	TERISTICS				•	
Non-Saturate	ed Switching Times					
t _{on}	Turn-On Time	$R_{L} = 100\Omega, I_{F} = 1mA, V_{CC} = 5V$		5		μs
t _{off}	Turn-Off Time	$R_{L} = 100\Omega, I_{F} = 1mA, V_{CC} = 5V$		5		μs

*Typical values at $T_A = 25^{\circ}C$

查询"H11AG1M"供应商 Safety and Insulation Ratings

As per IEC 60747-5-2, this optocoupler is suitable for "safe electrical insulation" only within the safety limit data. Compliance with the safety ratings shall be ensured by means of protective circuits.

Symbol	Parameter	Min.	Тур.	Max.	Unit
	Installation Classifications per DIN VDE 0110/1.89 Table 1				
	For Rated Main Voltage < 150Vrms		I-IV		
	For Rated Main voltage < 300Vrms		I-IV		
	Climatic Classification		55/100/21		
	Pollution Degree (DIN VDE 0110/1.89)		2		
CTI	Comparative Tracking Index	175			
V _{PR}	Input to Output Test Voltage, Method b, $V_{IORM} \times 1.875 = V_{PR}$, 100% Production Test with tm = 1 sec, Partial Discharge < 5pC	1594			V _{peak}
	Input to Output Test Voltage, Method a, $V_{IORM} \times 1.5 = V_{PR}$, Type and Sample Test with tm = 60 sec, Partial Discharge < 5pC	1275			V _{peak}
V _{IORM}	Max. Working Insulation Voltage	850			V _{peak}
V _{IOTM}	Highest Allowable Over Voltage	6000			V _{peak}
	External Creepage	7			mm
	External Clearance	7			mm
	Insulation Thickness	0.5			mm
RIO	Insulation Resistance at Ts, V _{IO} = 500V	10 ⁹			Ω

查询"H11AG1M"供应商 Typical Performance Curves

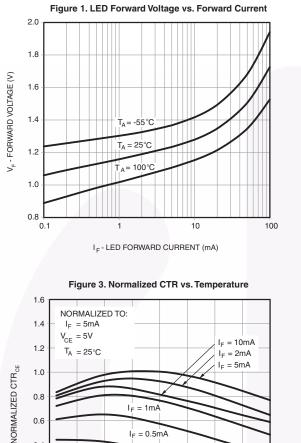
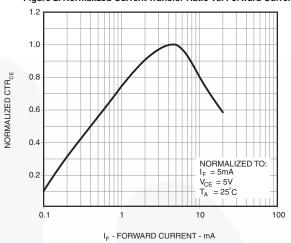


Figure 2. Normalized Current Transfer Ratio vs. Forward Current



0.6 $I_F = 0.5 mA$ 0.4 = 0.2mA 0.2 0.0 -60 -40 -20 0 20 40 60 80 100

TA - AMBIENT TEMPERATURE -°C

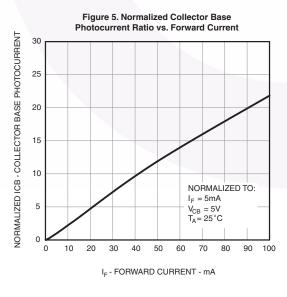


Figure 4. Normalized Collector vs. Collector - Emitter Voltage

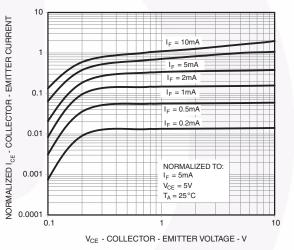
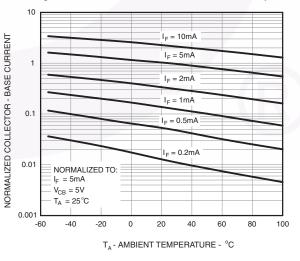


Figure 6. Normalized Collector - Base Current vs. Temperature





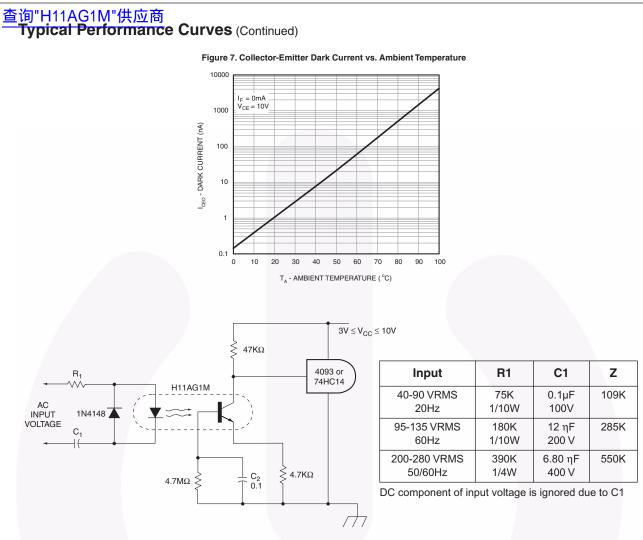
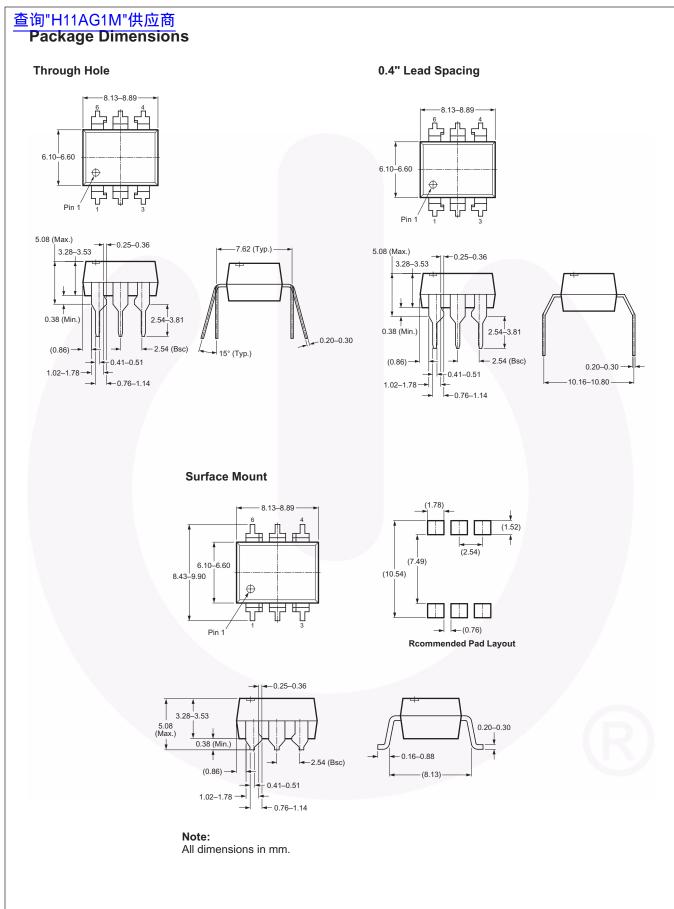


Figure 8. Telephone Ring Detector/A.C. Line CMOS Input Isolator

The H11AG1M uses less input power than the neon bulb traditionally used to monitor telephone and line voltages. Additionally. response time can be tailored to ignore telephone dial tap, switching transients and other undesired signals by modifying the value of C2. The high impedance to line voltage also can simply board layout spacing requirements.

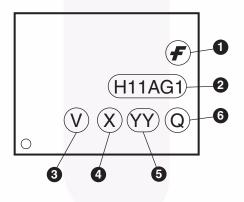


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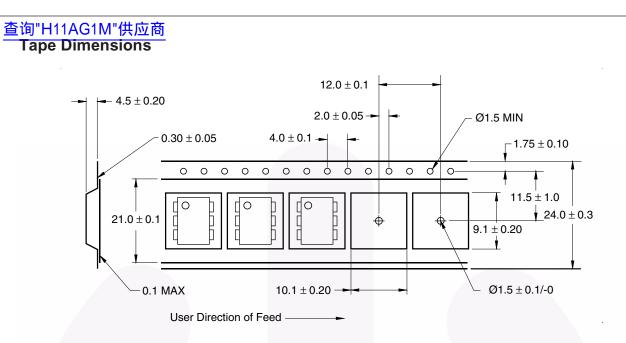
查询"H11AG1M"供应商 Ordering Information

Suffix	Example	Option
No Suffix	H11AG1M	Standard Through Hole Device (50 units per tube)
S	H11AG1SM	Surface Mount Lead Bend
SR2	H11AG1SR2M	Surface Mount; Tape and Reel (1,000 units per reel)
Т	H11AG1TM	0.4" Lead Spacing
V	H11AG1VM	VDE 0884
TV	H11AG1TVM	VDE 0884, 0.4" Lead Spacing
SV	H11AG1SVM	VDE 0884, Surface Mount
SR2V	H11AG1SR2VM	VDE 0884, Surface Mount, Tape & Reel (1,000 units per reel)

Marking Information



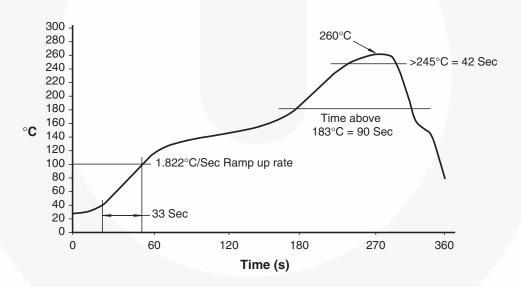
Definit	ions
1	Fairchild logo
2	Device number
3	VDE mark (Note: Only appears on parts ordered with VDE option – See order entry table)
4	One digit year code, e.g., '7'
5	Two digit work week ranging from '01' to '53'
6	Assembly package code



Note:

All dimensions are in inches (millimeters)





H11AG1M — Phototransistor Optocoupler

查询"H11AG1M"供应商

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